

## WEST Search History for Application 10797231

Creation Date: 2008121414:15

Query	DB	Op.	Plur.	Thes.	Date
(strained and MOSFET and SiGe)	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
((strained and MOSFET and SiGe) ) and (high k dielectric same "SiO.sub.2")	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
((strained and MOSFET and SiGe) ) and (high k dielectric same "SiO.sub.2" same gate)	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
((strained and MOSFET and SiGe) ) and (high k dielectric and ("SiO.sub.2" or oxide))	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
((strained and MOSFET and SiGe) ) and (high k dielectric and ("SiO.sub.2" or oxide) and gate)	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
((strained and MOSFET and SiGe) ) and (high k dielectric and ("SiO.sub.2" or oxide) and gate)	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
(strain\$ and MOSFET and SiGe)	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
(MOSFET and SiGe)	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
((MOSFET and SiGe) ) and (high k dielectric and ("SiO.sub.2" or oxide) and gate)	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-11-2008
(MODFET near10 MOSFET) and SIGe	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-14-2008
(MODFET near10 MOSFET) and SiGe	USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		12-14-2008